

TRIODE-HEPTODE

Triode-heptode intended for use as mixer in car radio sets and as sync separator in TV receivers.

QUICK REFERENCE DATATriode

Anode voltage	V _a	25	12.6	6.3	V
Anode current	I _a	2	0.75	0.3	mA
Transconductance	S	2.2	1.4	0.8	mA/V
Amplification factor	μ	20	18.3	14.6	-

Heptode as mixer

Anode voltage	V _a	25	12.6	6.3	V
Grids No.2 and 4 voltage	V _{g2+4}	25	12.6	6.3	V
Conversion conductance	S _c	450	220	90	μ A/V

Heptode as R.F. or I.F. amplifier

Anode voltage	V _a	25	12.6	6.3	V
Grids No.2 and 4 voltage	V _{g2+4}	25	12.6	6.3	V
Transconductance	S	1.5	0.75	0.35	mA/V

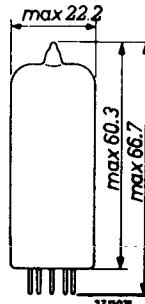
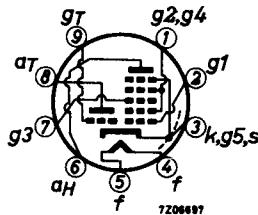
HEATING: Indirect by A.C. or D.C.; parallel or series supply

Heater voltage	V _f	6.3	V
Heater current	I _f	300	mA

DIMENSIONS AND CONNECTIONS

Dimensions in mm

Base: Noval



CAPACITANCESTriode section

Anode to all except grid	$C_{a(g)}$	2.1	pF
Grid to all except anode	$C_{g(a)}$	2.6	pF
Anode to grid	C_{ag}	1.0	pF

Heptode section

Anode to all	C_a	7.9	pF
Grid No.1 to all	C_{g_1}	4.8	pF
Anode to grid No.1	C_{ag_1}	max.	0.012 pF
Grid No.3 to all	C_{g_3}		6.0 pF
Grid No.1 to grid No.3	$C_{g_1g_3}$	max.	0.3 pF

Between heptode and triode sections

Anode heptode to anode triode	C_{aHaT}	0.20	pF
Anode heptode to grid triode	C_{aHgT}	max.	0.09 pF
Grid No.1 heptode to anode triode	C_{g_1HaT}	max.	0.06 pF
Grid No.1 heptode to grid triode	C_{g_1HgT}	max.	0.17 pF
Grid No.1 heptode to grid triode and grid No.3	C_{g_1H/gTg_3}	max.	0.45 pF
Anode heptode to grid triode and grid No.3	C_{aH/gTg_3}	max.	0.35 pF

TYPICAL CHARACTERISTICSTriode section

Anode voltage	V_a	25	12.6	6.3	V
Grid voltage	V_g	1)	1)	1)	-
Anode current	I_a	2	0.75	0.3	mA
Transconductance	S	2.2	1.4	0.8	mA/V
Amplification factor	μ	20	18.3	14.6	-

1) Obtained by grid current biasing: $R_g = 47 \text{ k}\Omega$.

OPERATING CHARACTERISTICS

Heptode as mixer, circuit fig.1.

Anode voltage	V _a	25	12.6	6.3	V
Grids No.2 and 4 voltage	V _{g2+4}	25	12.6	6.3	V
Grid No.1 voltage	V _{g1}	1)	1)	1)	
Oscillator voltage	V _{osc}	3.5	1.7	1.1	V _{RMS}
Grid No.3 resistor	R _{g3}	47	47	47	kΩ
Grid No.3 current	I _{g3}	40	18	7	μA
Anode current	I _a	550	170	50	μA
Grids No.2 and 4 current	I _{g2+4}	1000	300	80	μA
Conversion conductance	S _c	450	220	90	μA/V
Internal resistance	R _i	0.5	1.5	1.3	MΩ

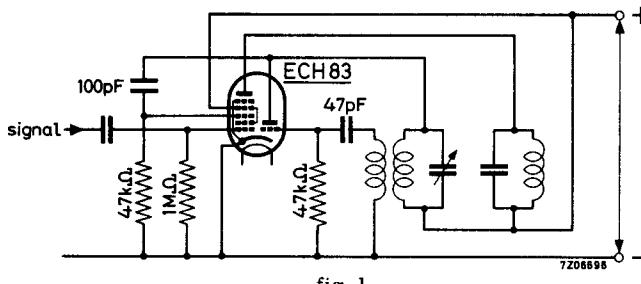


fig. 1

Heptode as R.F. or I.F. amplifier

Anode voltage	V _a	25	12.6	6.3	V
Grids No.2, No.3 and No.4 voltage	V _{g2+3+4}	25	12.6	6.3	V
Grid No.1 voltage	V _{g1}	1)	1)	1)	
Anode current	I _a	1.25	0.4	0.11	mA
Grids No.2, No.3 and 4 current	I _{g2+3+4}	0.85	0.25	0.08	mA
Transconductance	S	1.5	0.75	0.35	mA/V
Internal resistance	R _i	0.2	0.85	0.6	MΩ
Equivalent noise resistance	R _{eq}	5	6.5	8.5	kΩ

1) Obtained by grid current biasing: R_{g1} = 1 MΩ.

LIMITING VALUES (Design centre rating system)Triode section

Anode voltage	V_{a_0}	max.	550	V
	V_a	max.	250	V
Anode dissipation	W_a	max.	0.8	W
Cathode current	I_k	max.	6.5	mA
Grid resistor	R_g	max.	3	MΩ
Cathode to heater voltage	V_{kf}	max.	150	V
D.C. component		max.	100	V

Heptode section

Anode voltage	V_{a_0}	max.	550	V
	V_a	max.	50	V
Grids No.2 and 4 voltage	V_{g2+4}	max.	50	V
Cathode current	I_k	max.	5	mA
Grid No.1 resistor	R_{g1}	max.	3	MΩ
Grid No.3 resistor	R_{g3}	max.	50	kΩ
Cathode to heater voltage	V_{kf}	max.	150	V
D.C. component		max.	100	V

PHILIPS

Data handbook



**Electronic
components
and materials**

ECH83

page	sheet	date
1	1	1969.12
2	2	1969.12
3	3	1969.01
4	4	1969.12
5	FP	1999.08.15